L Number			- DD	I Time atoms
		Search Text	DB USPAT;	Time stamp 2002/10/31 18:32
-	1	("5319229").PN.	US-PGPUB	2002/10/31 18.32
			USPAT	2002/10/31 18:22
-	14	5319229.URPN.	i .	2002/10/31 18:22
! -	83	("gate dielectric" SAME ("high K" or "high	USPAT;	2002/11/01 09.38
		dielectric") same (oxide or SiO or	US-PGPUB	
		"SiO.sub.2" or dioxide)) and ((nitrogen		
		with (implant or implanting or implanted)		1
	,	or nitrida\$ or nitriting or nitritating or	[†
		nitriding or nitrided))		
_	16	("3668004" "3730766" "3967310"	USPAT	2002/10/31 18:58
		"4335391" "4495219" "4636833"		
		"4659606" "4690846" "4891684"		
		"4937650" "4989056" "5072269"	1	
	1	"5091761" "5111355" "5173835"		
		"5225286").PN.		
_	4	(("high k" or "high dielectric") WITH	USPAT;	2002/10/31 19:23
		(oxide or nitride or dioxide or	US-PGPUB	
	,	oxynitride)) SAME (anneal\$) SAME		
		(silicate)		
	38	("gate insulator" SAME ("high K" or "high	USPAT;	2002/11/01 09:40
]	dielectric" or "metal oxide") same (oxide	US-PGPUB	
		or SiO or "SiO.sub.2" or dioxide)) and		
		((nitrogen with (implant or implanting or		
		implanted) or nitrida\$ or nitriting or		
		nitritating or nitridas or nitriting of nitritating or nitridad or		
		nitrification)) .	USPAT;	2002/11/01 11:46
-	1109		US-PGPUB	2002/11/01 11:40
	i	oxide" or "hafnium oxide" or HfO or	US-FGFUB	
	İ	"zirconium oxide" or "ZrO.sub.2" or		
		"tantalum oxide" or "titanium dioxide" or	1	
		"TiO.sub.2" or "cesium oxide" or		
		"lantanum" or "tungsten oxide" or yttrium		
		or BSO or BST or BSrO or PZN or PZT or		
		PST) SAME (dioxide or "silicon oxide" or		
		SiO or "SiO.sub.2" or oxynitride or SiON		
		or SiN or "nitride")		
_	231	((anneal\$ or RTP or RTA) SAME ("metal	USPAT;	2002/11/01 10:27
		oxide" or "hafnium oxide" or HfO or	US-PGPUB	
		"zirconium oxide" or "ZrO.sub.2" or		
		"tantalum oxide" or "titanium dioxide" or		
		"TiO.sub.2" or "cesium oxide" or		
		"lantanum" or "tungsten oxide" or yttrium		,
		or BSO or BST or BSrO or PZN or PZT or		
		PST) SAME (dioxide or "silicon oxide" or		
	1	SiO or "SiO.sub.2" or oxynitride or SiON	•	
		or SiN or "nitride")) and (silicate)		
_	36		USPAT;	2002/11/01 10:27
	1	oxide" or "hafnium oxide" or HfO or	US-PGPUB	
		"zirconium oxide" or "ZrO.sub.2" or		
		"tantalum oxide" or "titanium dioxide" or		
	i	"TiO.sub.2" or "cesium oxide" or		
	1	"lantanum" or "tungsten oxide" or yttrium		
		or BSO or BST or BSrO or PZN or PZT or		‡
		or BSO or BST or BSIO of PZN of PZI of		
	1	PST) SAME (dioxide or "silicon oxide" or		
		SiO or "SiO.sub.2" or oxynitride or SiON		
		or SiN or "nitride")) SAME silicate	HCDM.	2002/11/01 10:51
•	357	(438/287).CCLS.	USPAT;	2002/11/01 10:51
-	1		US-PGPUB	2002/11/01 10:57
-	1	(438/217).CCLS.	USPAT;	2002/11/01 10:57
_	271	(130/21/).0023.		
-	271		US-PGPUB	0000/11/01 11 01
-	271 1477	((composite or alternate or alternating)	USPAT;	2002/11/01 11:01
-			1	2002/11/01 11:01
-		((composite or alternate or alternating) WITH (insulator or dielectric or insulating)) SAME gate	USPAT; US-PGPUB	
- - -		((composite or alternate or alternating) WITH (insulator or dielectric or insulating)) SAME gate	USPAT; US-PGPUB USPAT;	2002/11/01 11:01
-	1477	((composite or alternate or alternating) WITH (insulator or dielectric or insulating)) SAME gate (((composite or alternate or alternating) WITH (insulator or dielectric or	USPAT; US-PGPUB	
-	1477	((composite or alternate or alternating) WITH (insulator or dielectric or insulating)) SAME gate (((composite or alternate or alternating) WITH (insulator or dielectric or insulating)) SAME gate) and ("high k" or	USPAT; US-PGPUB USPAT;	
- - -	1477	((composite or alternate or alternating) WITH (insulator or dielectric or insulating)) SAME gate (((composite or alternate or alternating)	USPAT; US-PGPUB USPAT;	



			·	0000 (11 (01 11 46)
-	32	((((composite or alternate or alternating)	USPAT;	2002/11/01 11:46
		WITH (insulator or dielectric or insulating)) SAME gate) and ("high k" or	US-PGPUB	
		"higher k" or "higher dielectric" or "high		
_	1270	dielectric")) and silicate ("metal oxide" or "hafnium oxide" or HfO	USPAT;	2002/11/01 12:38
		or "zirconium oxide" or "ZrO.sub.2" or	US-PGPUB	
		"tantalum oxide" or "Ta.sub.2 O.sub.5" or "titanium dioxide" or "TiO.sub.2" or		
		"cesium oxide" or "lantanum" or "tungsten		
		oxide" or yttrium or BSO or BST or BSrO or		
		PZN or PZT or PST) WITH (reacting or reacted or react or reaction) WITH		
		(silicate or silicon)	HODAM.	2002/11/01 12:39
-	150	(("metal oxide" or "hafnium oxide" or HfO or "zirconium oxide" or "ZrO.sub.2" or	USPAT; US-PGPUB	2002/11/01 12:39
		"tantalum oxide" or "Ta.sub.2 O.sub.5" or	1	
		"titanium dioxide" or "TiO.sub.2" or		
		"cesium oxide" or "lantanum" or "tungsten oxide" or yttrium or BSO or BST or BSrO or		
		PZN or PZT or PST) WITH (reacting or		!
		reacted or react or reaction) WITH (silicate or silicon)) and gate		
_	5	("5441906" "5668024" "5691225"	USPAT	2002/11/01 13:09
		"5780362" "5807770").PN.		0000/11/01 13 10
-	4	5904517.URPN.	USPAT	2002/11/01 13:10